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SEMICONDUCTOR TM

FDR858P

Single P-Channel, Logic Level, PowerTrench[™] MOSFET

General Description

The SuperSOT-8 family of P-Channel Logic Level MOSFETs have been designed to provide a low profile, small footprint alternative to industry standard SO-8 little foot type product.

This P-Channel Logic Level MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

These devices are well suited for notebook computer applications: load switching and power management, battery charging circuits, and DC/DC conversion.

Features

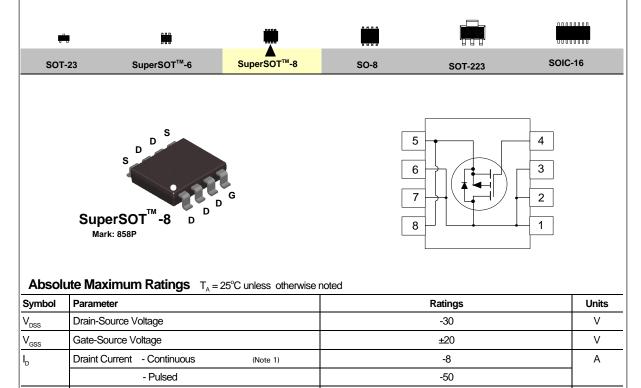
- -8 A, -30 V. $R_{DS(ON)} = 0.019 \ \Omega @ V_{GS} = -10 V$, $\mathsf{R}_{\mathrm{DS(ON)}} = 0.028 \ \Omega @ \mathsf{V}_{\mathrm{GS}} = -4.5 \ \mathsf{V}.$
- Low gate charge (21nC typical).

1.8

 High performance trench technology for extremely low R_{DS(ON)}.

February 1999

SuperSOT[™]-8 package: small footprint (40%) less than SO-8); low profile (1mm thick); maximum power comperable to SO-8.



1 (Note 1c) 0.9 $\mathsf{T}_{\mathsf{J}},\mathsf{T}_{\mathsf{STG}}$ Operating and Storage Temperature Range -55 to 150 THERMAL CHARACTERISTICS $\mathsf{R}_{_{\theta \mathsf{J}\mathsf{A}}}$ Thermal Resistance, Junction-to-Ambient (Note 1a) 70 Thermal Resistance, Junction-to-Case 20 $R_{\mu JC}$ (Note 1)

(Note 1a)

(Note 1b)

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Maximum Power Dissipation

 P_{D}

W

°C

°C/W

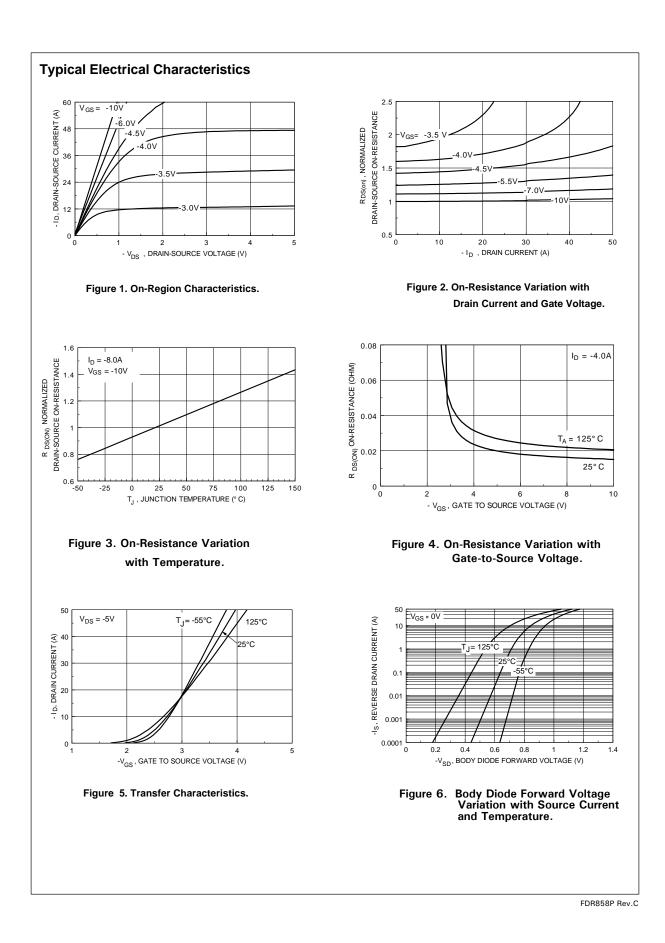
°C/W



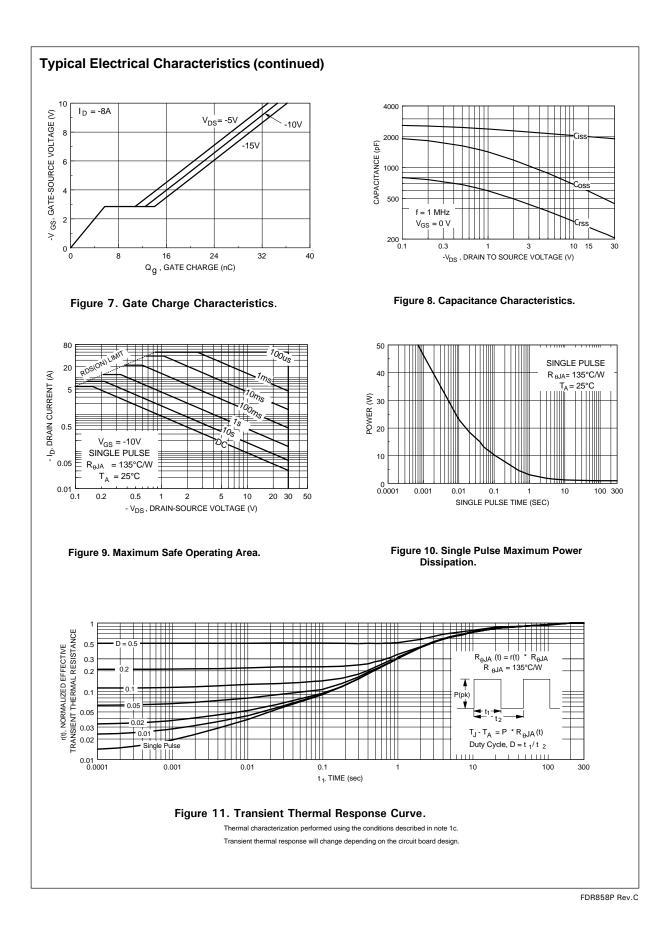
OFF CHARA		Conditions	Min	Тур	Max	Units
	CTERISTICS					
	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-30			V
$\Delta BV_{DSS}/\Delta T_{J}$		$I_{\rm D}$ = -50 µA, Referenced to 25 °C		-22		mV /⁰C
	Zero Gate Voltage Drain Current	$V_{DS} = -24 V, V_{GS} = 0 V$			-1	μA
200	°	T ₁ = 55°C			-10	μA
GSS	Gate - Body Leakage Current	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
GSS		$V_{GS} = -20 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$			-100	nA
	TERISTICS (Note 2)		1			
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-1	-1.7	-3	V
$\Delta V_{GS(th)} / \Delta T_J$		$I_{\rm D}$ = -50 µA, Referenced to 25 °C		4		mV /°C
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -8 \text{ A}$		0.0155	0.019	Ω
		T_= 125°C		0.021	0.03	1
		$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -6.3 \text{ A}$		0.022	0.028	
D(ON)		$V_{GS} = -10 \text{ V}, \text{ V}_{DS} = -5 \text{ V}$	-50			А
D _{FS}		$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -3.2 \text{ A}$		25		S
DYNAMIC CH	IARACTERISTICS					
C _{iss}	Input Capacitance	$V_{DS} = -15 \text{ V}, \ V_{GS} = 0 \text{ V},$		2010		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		590		pF
C _{rss}	Reverse Transfer Capacitance			260		pF
SWITCHING (CHARACTERISTICS (Note 2)					
D(on)	Turn - On Delay Time	$V_{DD} = -15 V, I_{D} = -1 A,$		12	22	ns
T	Turn - On Rise Time	$V_{GS} = -10V, R_{GEN} = 6 \Omega$		15	27	ns
D(off)	Turn - Off Delay Time			100	140	ns
f	Turn - Off Fall Time			55	80	ns
С ^а	Total Gate Charge	$V_{DS} = -15 \text{ V}, \ I_{D} = -8 \text{ A},$		21	30	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = 5 V$		6		nC
Q _{gd}	Gate-Drain Charge			8		nC
DRAIN-SOU	IRCE DIODE CHARACTERISTICS AND MAXIM	MUM RATINGS				
s	Maximum Continuous Drain-Source Diode Forwa	ard Current			-0.67	А
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 V, I_{S} = -0.67 A$ (Note 2)		-0.7	-1.2	V

2. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2.0%.

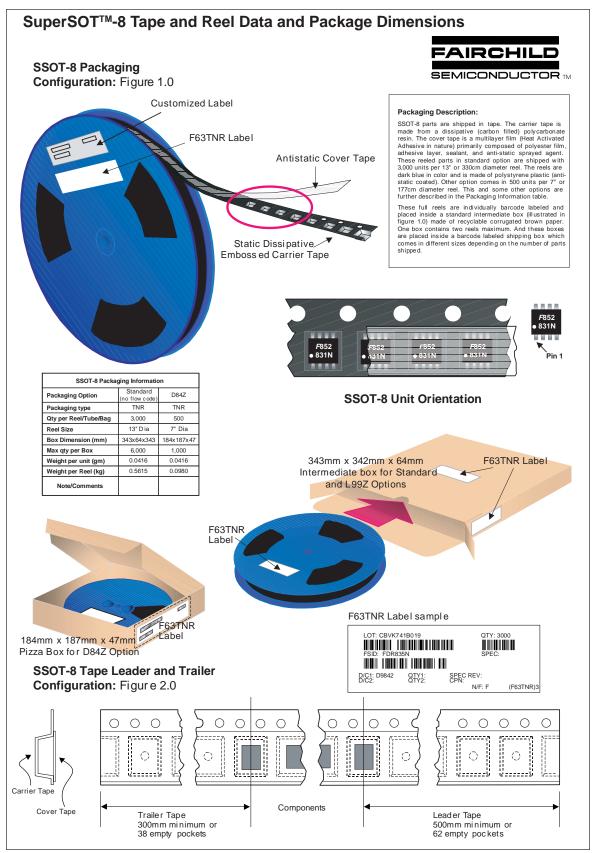






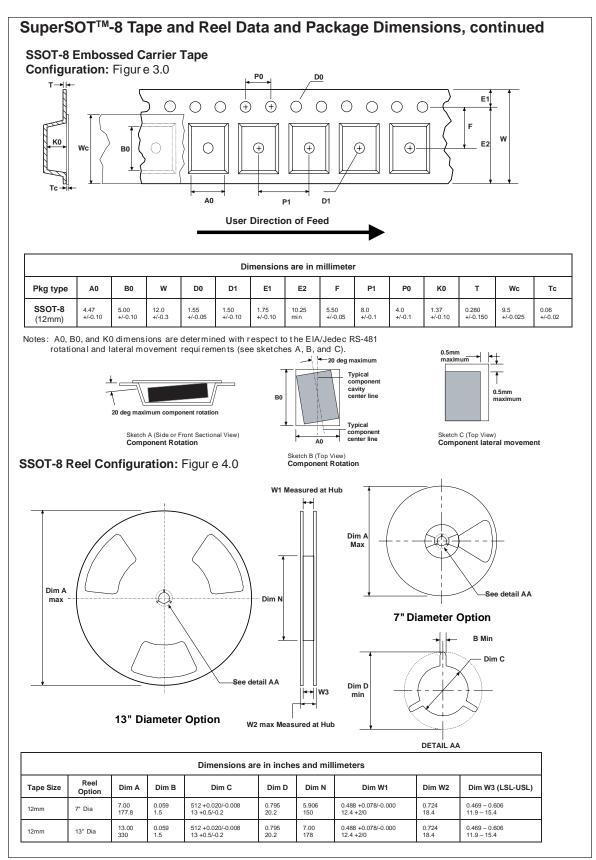






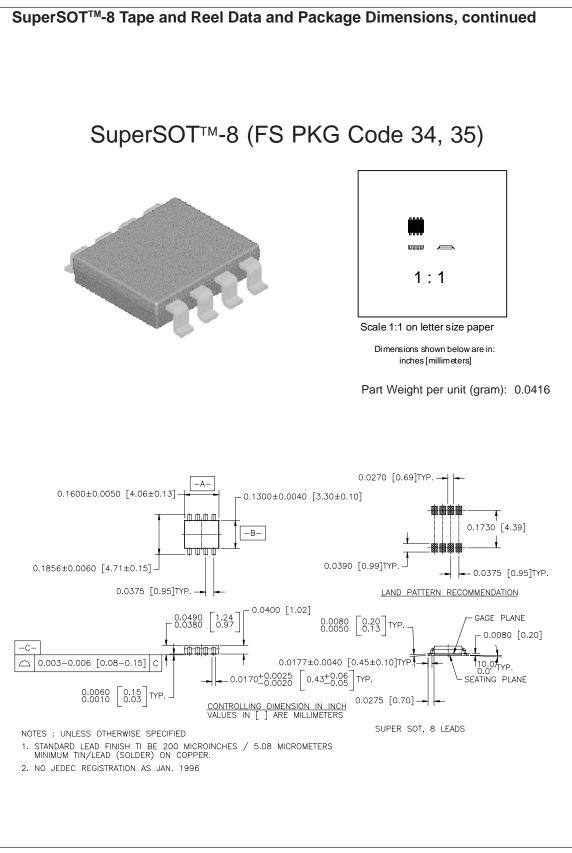
August 1999, Rev. C





July 1999, Rev. C





September 1998, Rev. A



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